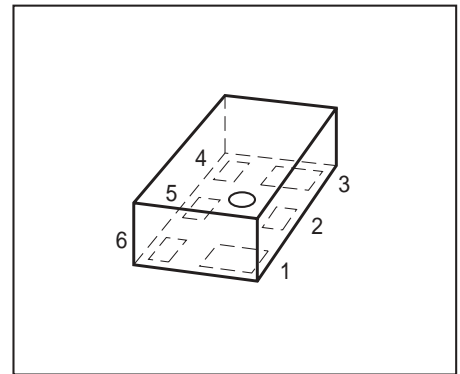
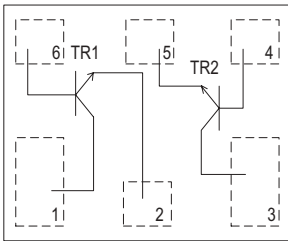


NPN Silicon RF Transistor*

- Low voltage/ Low current operation
- For low noise amplifiers
- For Oscillators up to 3.5 GHz and Pout > 10 dBm
- Low noise figure: 1.0 dB at 1.8 GHz
- Built in 2 transistors (TR1, TR2: die as BFR360L3)
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



* Short term description



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFS360L6	FB	1=C1	2=E1	3=C2	4=B2	5=E2	6=B1	TSLP-6-1

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	6	V
Collector-emitter voltage	V_{CES}	15	
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	35	mA
Base current	I_B	4	
Total power dissipation ²⁾ $T_S \leq 101^\circ\text{C}$	P_{tot}	210	mW
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

¹Pb-containing package may be available upon special request

² T_S is measured on the collector lead at the soldering point to the pcb

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 230	K/W

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	6	9	-	V
Collector-emitter cutoff current $V_{CE} = 15 \text{ V}, V_{BE} = 0$	I_{CES}	-	-	10	μA
Collector-base cutoff current $V_{CB} = 5 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1 \text{ V}, I_C = 0$	I_{EBO}	-	-	1	μA
DC current gain $I_C = 15 \text{ mA}, V_{CE} = 3 \text{ V}$, pulse measured	h_{FE}	90	120	160	-

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

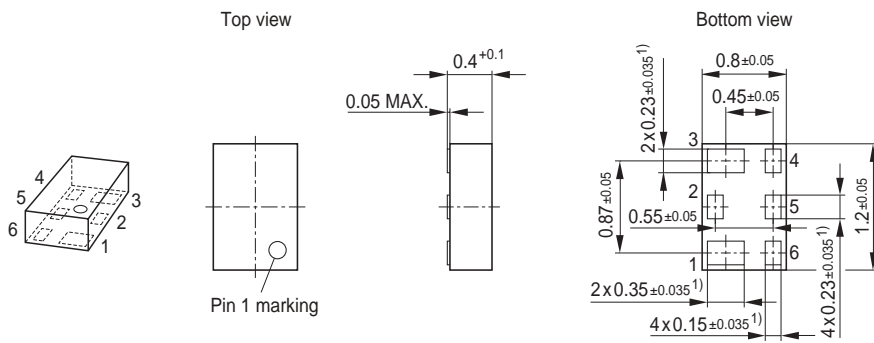
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 1\text{ GHz}$	f_T	10	14	-	GHz
Collector-base capacitance $V_{CB} = 5\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.26	0.4	pF
Collector emitter capacitance $V_{CE} = 5\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.14	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	0.42	-	
Noise figure $I_C = 3\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $f = 1.8\text{ GHz}$ $I_C = 3\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $f = 3\text{ GHz}$	F_{min}	-	1 1.5	-	dB
Power gain, maximum available ¹⁾ $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$ $f = 3\text{ GHz}$	G_{ma}	-	16.5 11.5	-	
Transducer gain $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 1.8\text{ GHz}$ $f = 3\text{ GHz}$	$ S_{21e} ^2$	-	13.5 9.5	-	dB
Third order intercept point at output ²⁾ $V_{CE} = 3\text{ V}$, $I_C = 15\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\Omega$	IP_3	-	24	-	dBm
1dB Compression point at output $I_C = 15\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 1.8\text{ GHz}$	P_{-1dB}	-	9	-	

$$^1 G_{ma} = |S_{21e} / S_{12e}| (k - (k^2 - 1)^{1/2})$$

²⁾IP3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz

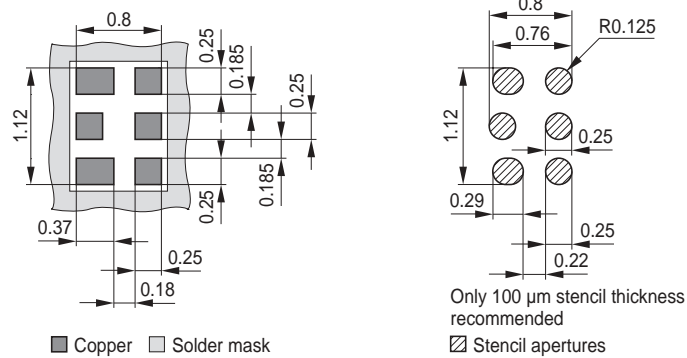
Package Outline



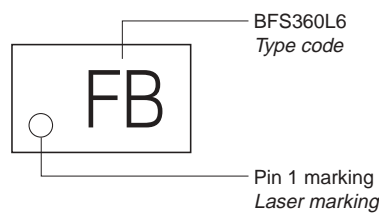
1) Dimension applies to plated terminal

Foot Print

For board assembly information please refer to Infineon website "Packages"

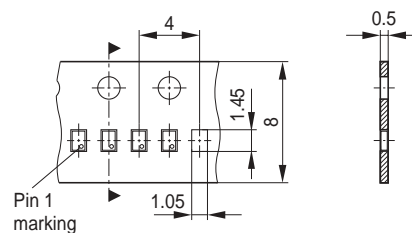


Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 15.000 Pieces/Reel



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